

Supplementary Information

Redox-mediated conversion of atomically dispersed platinum to sub-nanometer particles

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S1. Sn deposition on Pt–CeO₂ film in an oxygen atmosphere

The Sn 4d and Pt 4f spectra obtained from the 10% Pt–CeO₂ film following the Sn deposition in an oxygen atmosphere are shown in Figure S1a and S1b, respectively. The Pt 4f spectrum obtained from 10% Pt–CeO₂ film prior to Sn deposition (bottom trace, Figure 1b) contains a doublet at 73.0 eV (Pt 4f_{7/2}) associated with Pt²⁺ species.

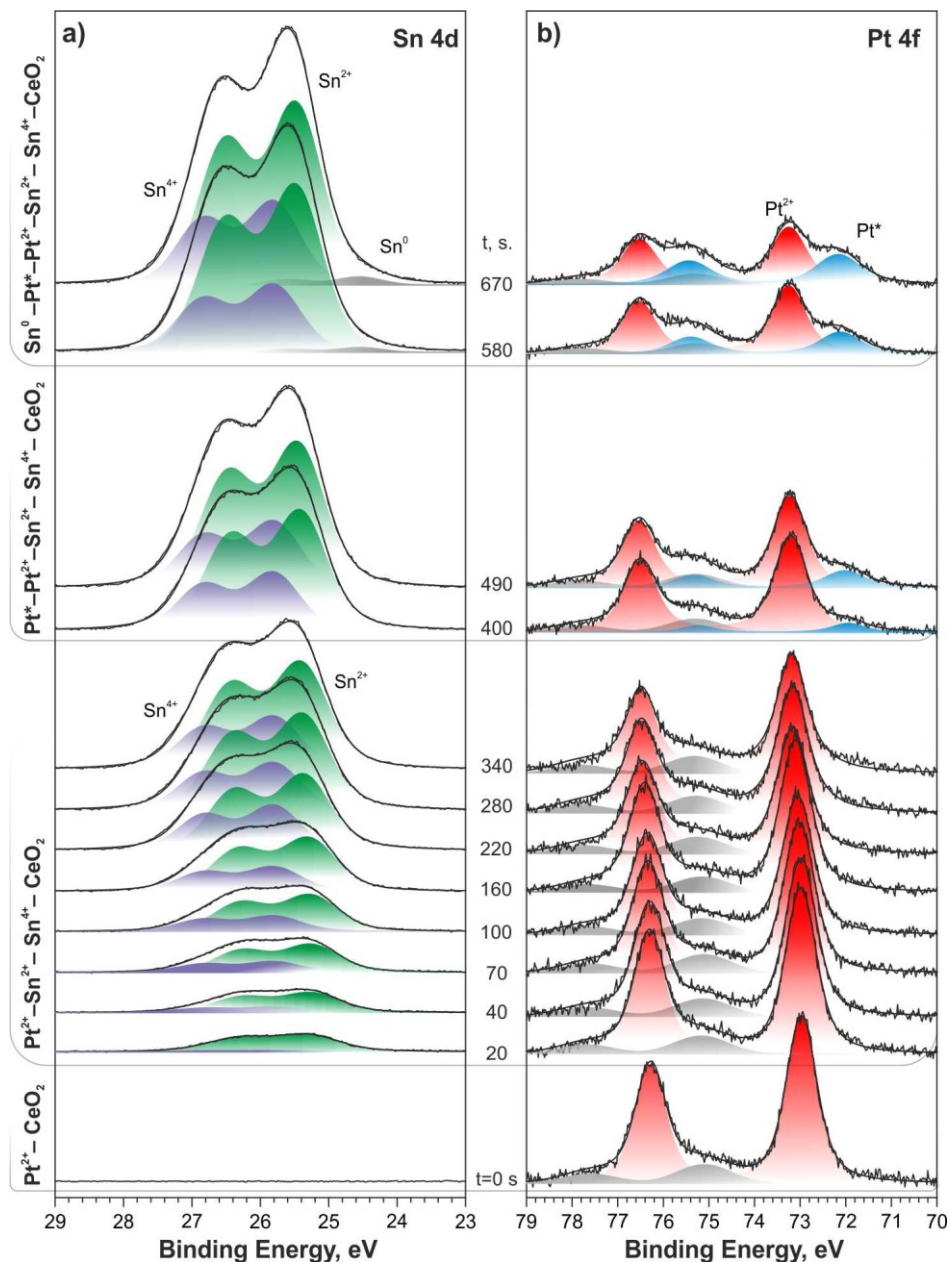


Figure S1. Sn 4d (a) and Pt 4f (b) spectra obtained from 10% Pt–CeO₂ film during stepwise Sn deposition at 300 K in O₂ atmosphere. The spectra were obtained with photon energies of 60 eV (Sn 4d) and 180 eV (Pt 4f).

Additionally, a minor contribution from the underlying Cu(111) substrate associated with the Cu 3p core level emerges at 75.0 eV (Cu 2p_{3/2}).

The deposition of Sn under an oxygen atmosphere gives rise to two doublets in the Sn 4d spectra at 25.3 eV (4d_{5/2}) and 25.8 eV (4d_{3/2}). The corresponding peaks were assigned to Sn²⁺ ions in a Sn–Ce oxide and Sn⁴⁺ ions in SnO₂ or Ce₂Sn₂O₈ phases.^{S1-3} Both peaks grow in intensity as a function of the Sn deposition time (Figure S1).

The development of the integrated Pt* intensities upon Sn deposition in UHV and in oxygen atmosphere is plotted in Figure S2 as a function of the integrated Sn²⁺ intensity.

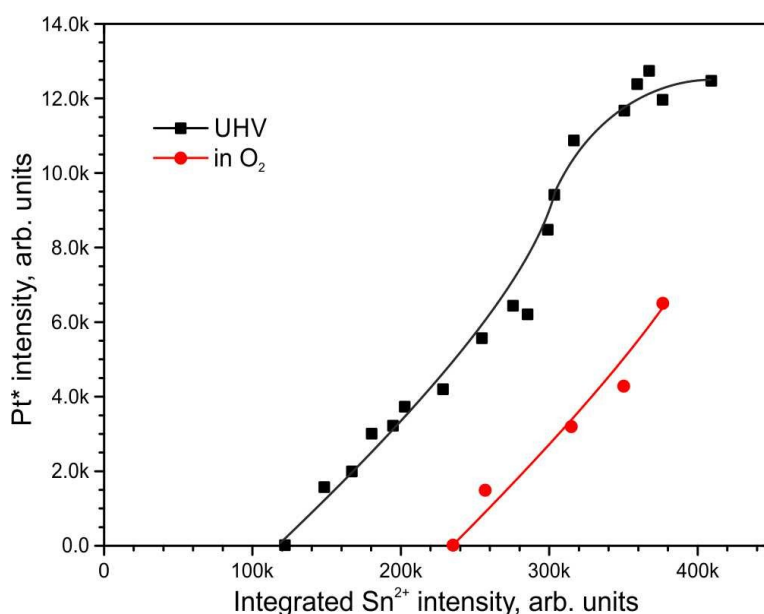


Figure S2. Development of the Pt 4f spectral contribution from ultra-small Pt* nanoparticles as a function of the integrated Sn²⁺ intensity on a 10% Pt–CeO₂ film during stepwise deposition of Sn at 300 K in UHV (black squares) and in O₂ atmosphere (red circles).

S2. The onset of Pt²⁺ reduction and formation of sub-nanometer particles

The circumstances of Pt²⁺ reduction has been investigated with respect to the reduction degree of 10% Pt–CeO₂ film caused by Sn deposition under UHV.

Based on the concentrations of Ce³⁺ and Pt²⁺ species summarized in Table S1, we determined the corresponding number of Ce³⁺ ions at the onset of the Pt²⁺ reduction. We found that the emergence of 6 Ce³⁺ centers triggers the reduction of one Pt²⁺ species.

Table S1. Experimental estimation of the threshold ratio between the number of Ce^{3+} centers formed and Pt^{2+} ions reduced upon Sn deposition on the 10% Pt– CeO_2 film at 300 K in UHV.^a

t [s]	RER	Stoichiometry $\text{Ce}^{3+}/\text{Ce}^{4+}$	$\Delta\text{N}(\text{Ce}^{3+})$ [10^{18} m^{-2}]	$\text{N}(\text{Ce}^{3+})$ [10^{18} m^{-2}]	$\text{N}(\text{Pt}^{2+})$ [10^{18} m^{-2}]	$\Delta\text{N}(\text{Pt}^{2+})$ [10^{18} m^{-2}]	$\text{N}(\text{Ce}^{3+})/\Delta\text{N}(\text{Pt}^{2+})$
0	0.12	0.0218	0	0	2.104		
100	0.95	0.1719	0.9027	0.9027	2.098		
120	1.10	0.1990	1.1951	1.5713	1.8392	0.265	5.93

^aColumns from left to right: Sn deposition time; resonant enhancement ratio; $\text{Ce}^{3+}/\text{Ce}^{4+}$ concentration ratio; the change in the concentration of Ce^{3+} cations; total number of Ce^{3+} cations formed upon Sn deposition; Pt^{2+} density; the number of reduced Pt^{2+} species that corresponds to the number of formed Pt^* species; ratio of the total number of Ce^{3+} centers and the number of reduced Pt^{2+} species (the number of formed Pt^* species).

S3. Profiling the depth distribution of Sn in the Pt– CeO_2 film

The depth distribution of Sn in the 5% Pt– CeO_2 film has been investigated by means of the software for simulation of electron spectra for surface analysis SESSA 1.1.^{S4} The analysis involves simulation of core level intensities based on the given structure and composition of the film. Thus, numerous model systems were assembled with respect to the Sn distribution in the 5% Pt– CeO_2 film. The intensities of the Sn 3d (Sn^{2+} contribution), Ce 3d (a sum of Ce^{4+} and Ce^{3+} contributions), and O 1s core levels were simulated for each of the model. Then, the ratios of Sn/O and Ce/O intensities were determined and compared with the experimentally obtained values. In Figure S3, the experimental (symbols) and simulated (lines) Sn/O and Ce/O intensities are compared for two deposition times, t' and t'' .

The deposition of the corresponding amounts of Sn on the 5% Pt– CeO_2 film at both deposition times yielded exclusively Sn^{2+} ions associated with the formation of Sn–Ce oxide, i.e. it did not involve the formation of metallic Sn^0 particles.

For the deposition time t' , the distribution of Sn was considered at the surface (models A–D) and in the bulk of 5% Pt– CeO_2 film without (E, F) and with (model G) subsequent intermixing with Ce cations (see Figure S3a).

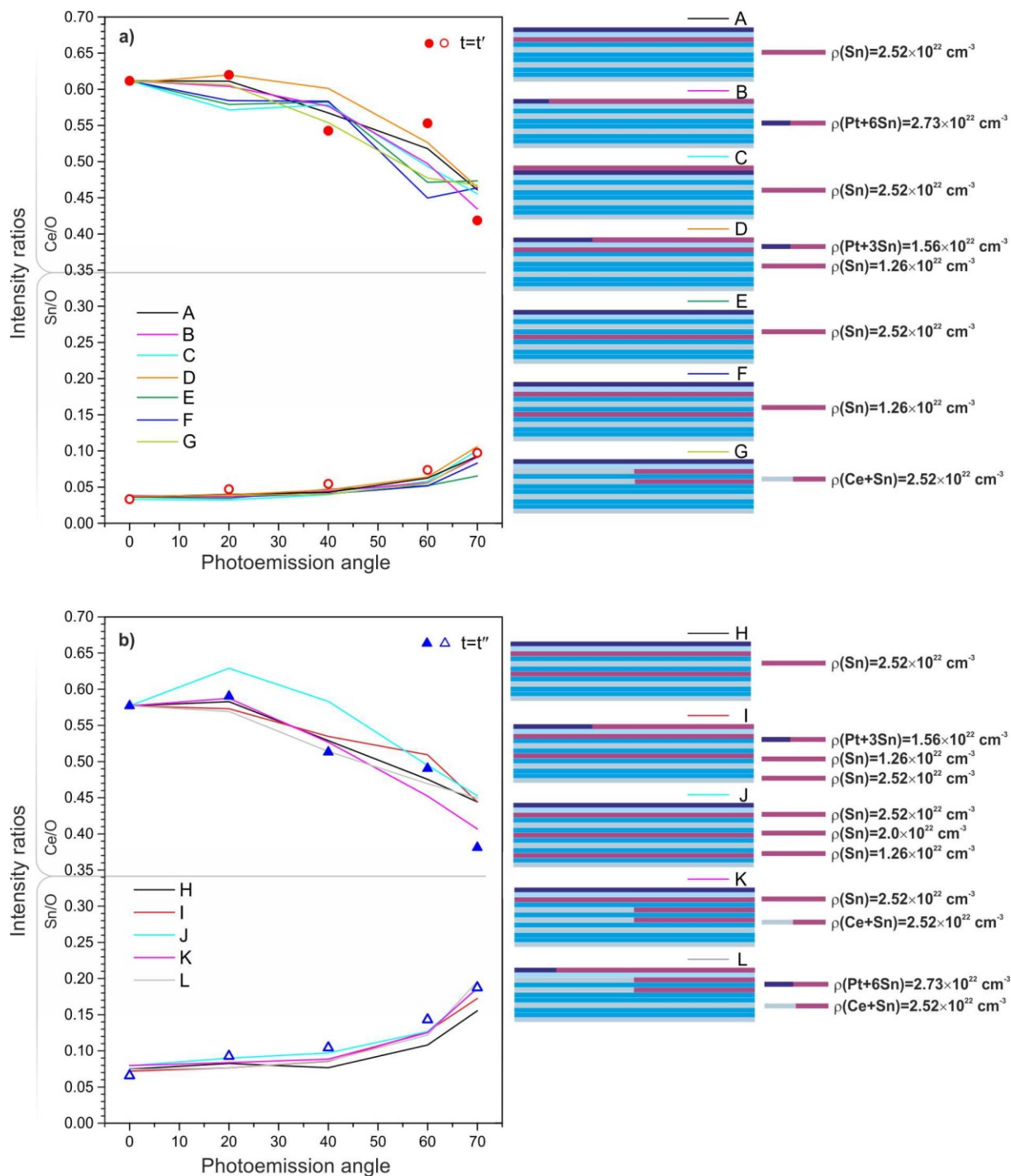


Figure S3. The ratio of the total intensities of Ce 3d to O 1s (Ce/O, top panel) and the ratio of Sn²⁺ intensity in Sn 3d to O 1s (Sn/O, bottom panel) obtained at different photoemission angles from 5% Pt–CeO₂ film after the Sn deposition times t' (a) and t'' (b) at 300 K in UHV. The corresponding models for the Sn-deposited 5% Pt–CeO₂ film are shown on the right.

The most distinct differences between the simulated and experimentally obtained Ce/O intensity ratios were observed for the models E-G concerned with the diffusion of Sn into the bulk. For these models, particularly incorrect trend in their angular functions was observed for the photoemission angles 60° and 70° .

Among the models A-D considering the Sn adsorption at the surface of 5% Pt–CeO₂ film, a good match was obtained with models A and B. In the model A, a Sn layer was placed below the low-density Pt–O layers. The model B considers Sn atoms to be adsorbed in the same layer with Pt²⁺ species. Both models A and B yielded similarly good match between the simulated and experimental Ce/O ratios (see Figure S3a). In contrast, the model C obtained by placing a Sn monolayer on top of Pt film did not produce a satisfactory match between the simulated and experimental Ce/O ratios (see Figure S3a).

Finally, we considered a combination of both models A and B represented by the model D (see Figure S3a). The model D yielded a fairly good match between the simulated and experimental Ce/O ratios. Based on the comparison of the simulated and experimental angular function for Ce/O and Sn/O ratios, we conclude that Sn atoms will predominantly occupy the surface sites and are likely to diffuse under the low-density Pt–O layers. At the same time, diffusion of Sn into the deeper layers, e.g. below the Ce layers, is ruled out.

For the deposition time t'' , we considered diffusion of Sn atoms into the bulk. Several models H-L were assembled followed by the comparison of the simulated and experimental angular functions of Ce/O and Sn/O ratios (see Figure S3b). The models H and I were built by combining the models A and E, and the models D and E, respectively. Thus, an additional Sn layer was inserted between the O–O layers below the first Ce layer. Additionally, the model J was built by inserting two Sn layers between the two O–O bulk layers of the model A, specifically, below the first and second Ce layers (see model J, Figure S3b). Here, we adjusted the Sn concentrations in the two bottom Sn layers to yield the best match with the experimental Sn/O ratios. No intermixing of Sn and Ce cations was considered in the models H-J.

Finally, the intermixing between the Sn and Ce cations was considered in the models K and L. Essentially, the model K was built on the basis of the model H by allowing the first Ce layer to intermix with bottom Sn layer at a ratio 1 to 1. Thus two mixed Ce/Sn layers were formed in the model K. Similarly, the model L was assembled based on the model B.

Overall, the best match between the simulated and experimental angular functions of Ce/O ratios was obtained with model K. Therefore, we conclude that at the deposition time t'' , Sn atom will diffuse into the bulk and intermix with the Ce cations from the first Ce layer. Yet, diffusion of Sn below the second Ce layer is unlikely.

S4. Temperature induced conversion of Pt^{2+} species in the absence of metallic Sn

The development of Sn 4d and Pt 4f spectra obtained from the 10% Pt– CeO_2 film after the last Sn deposition step under an oxygen atmosphere followed by annealing in UHV are shown in Figure S4a and S4b, respectively. The annealing of the 10% Pt– CeO_2 film promotes the reduction of Pt^{2+} species. However, the reduction of Pt^{2+} species is noticeably slower in comparison to the 10% Pt– CeO_2 film deposited with Sn under UHV. We relate the differences in the stabilities of Pt^{2+} species on two samples to the presence of metallic Sn^0 .

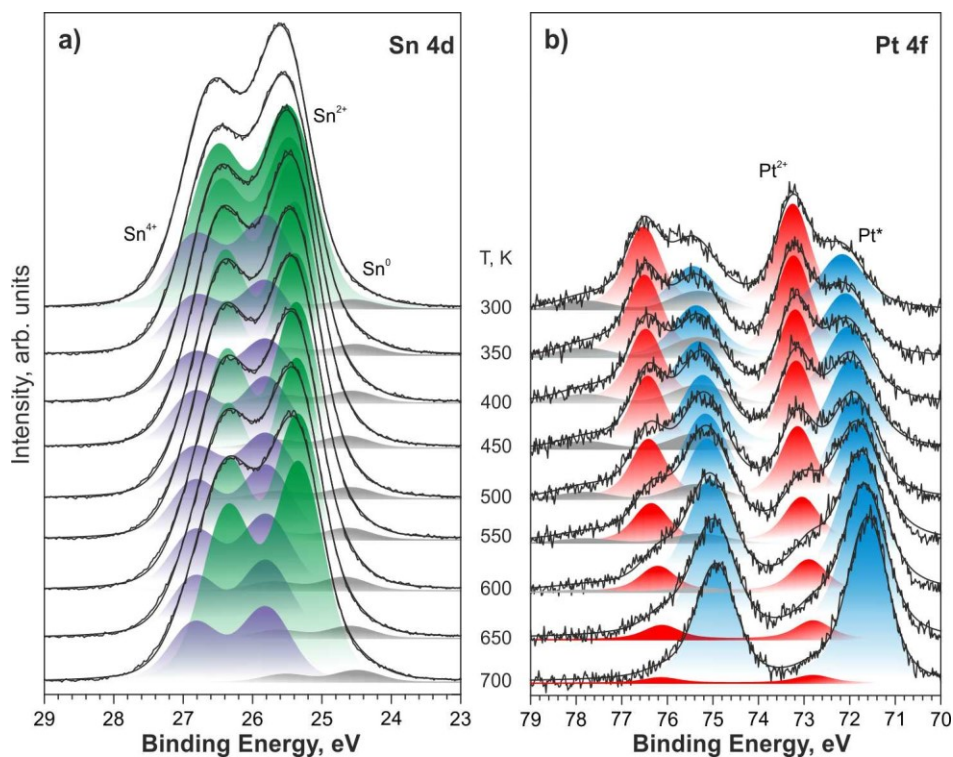


Figure S4. Sn 4d (a) and Pt 4f (b) spectra obtained during annealing of 10% Pt– CeO_2 after Sn deposition at 300 K in O_2 atmosphere. The spectra were obtained with photon energies of 60 eV (Sn 4d) and 180 eV (Pt 4f).

In particular, thermally triggered dissolution of Sn^0 into the bulk of the 10% Pt– CeO_2 film (see Section 3.4) results in the increase of Ce^{3+} centers and facilitates reduction of Pt^{2+} species. Therefore, in the absence of metallic Sn^0 , reduction of Pt^{2+} species requires higher annealing temperatures.

S5. The degree of reduction of Ce cations in the 5% Pt– CeO_2 film controlled by Sn

The Ce 3d spectra obtained from the 5% Pt– CeO_2 film before ($t=0$ s, 300 K) and after ($t=t''$, 300 K) the Sn deposition in UHV at 300 K followed by annealing to 700 K in UHV ($t=t'''$, 700 K) are shown in Figure S5.

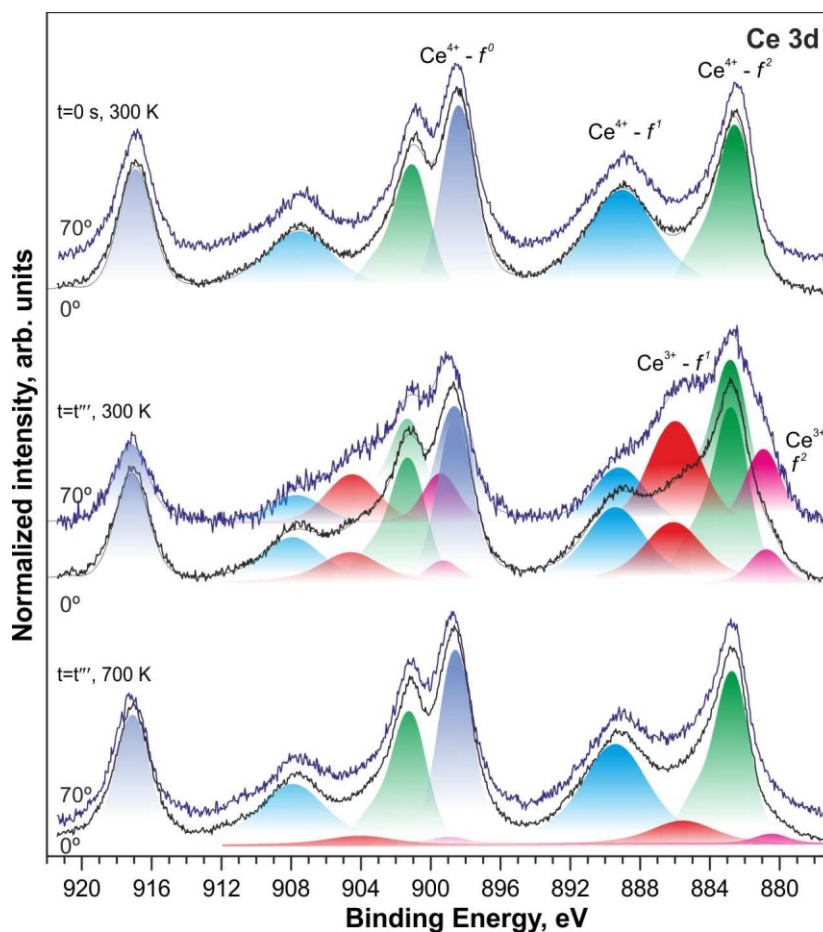


Figure S5. Ce 3d spectra obtained from 5% Pt– CeO_2 before (top) and after (middle) Sn deposition at 300 K followed by annealing to 700 K (bottom). The spectra were obtained at the photoemission angles 70° (dark blue) and 0° (black). The spectra were fitted with the multiple spectral contributions from Ce^{4+} and Ce^{3+} cations.

Here, the Ce 3d spectra obtained at the emission angles of 70° and 0° represent a chemical state of Ce cations at the surface and in the bulk, respectively. Prior to the Sn deposition, the Ce 3d spectra contain the contributions exclusively from the Ce⁴⁺ cations at both photoemission angles. Three components at the binding energies of 882.5, 889.0, and 898.4 eV arise due to three different final states during photoemission related to the occupancy of the *f*-states in Ce⁴⁺ cations. The deposition of Sn on the Pt–CeO₂ film in UHV results in the formation of Ce³⁺ centers associated with the emergence of two additional doublets at 880.9 and 886.0 eV. The corresponding doublets arise from two different final states related to the occupancy of *f*-states in Ce³⁺ centers. The comparison of the Ce 3d spectra at two photoemission angles, 70° and 0°, suggests higher concentration of Ce³⁺ at the surface.

This observation is consistent with the formation of Sn²⁺ preferentially close to the surface. As discussed in Section 3.3, the annealing of the 5% Pt–CeO₂ film after the deposition of Sn in UHV above 600 K resulted in the loss of Sn due to its dissolution in Cu(111). This process is accompanied by the re-oxidation of Ce³⁺ cations both in the bulk and at the surface (see Figure S5, bottom spectra). This yielded sub-nanometer Pt particles supported on practically Sn-free nearly stoichiometric CeO₂ film.

References

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